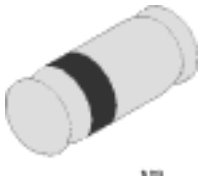
Switching Diode (FHLL4448)



Description

· The **FHLL4448** is designed for high-speed switching application in hybrid thick-and-thin-film circuits.

·Small surface mouting type.**(LL-34)**

ABSOLUTE MAXIMUM RATINGS 最大额定值(T_A=25℃)

RATING	Symbol	Value	Unit
Reverse Voltage 反向电压	V_R	75	V
Repetitive peak reverse voltage反向峰值电压	V_{RM}	100	V
Peak forward surge current正向浪涌电流(At tp=1 μ s)	I_{FSM}	2	A
Repetitive peak forward current正向峰值电流	I_{FRM}	500	mA
Forward current正向电流	I_F	300	mA
Average forward current 平均正向电流 (At V_R=0)	I_{FAV}	150	mA
Power Dissipation 耗散功率 at T_A =25℃	P_{TOT}	500	mW
Junction Temperature 结温	T_J	175	℃
Storage Temperature Range 存储温度	T_S	-65 to +175	℃

ELECTRICAL CHARACTERISTICS 电特性(T_A=25℃)

Characteristic 特性		Symbol	Min	Typ	Max	Unit
Forward Voltage 正向电压	At I_F=5mA	V_F	0.62	-	0.72	V
	At I_F=100mA		-	0.93	1.0	
Leakage current 漏电流 At V_R=20v At V_R=75v At V_R=20v, Tj=150℃		 I_R I_R I_R	 - - -	 - - -	 25 5 50	 nA μ A μ A
Reverse Breakage Voltage 反向击穿电压 I_R=100 μ A, t_p/T=0.01, t_p=0.3ms		$V_{(BR)R}$	100	-	-	V
Capacitance 电容 At V_R=0,f=1.0MHz, V_{HF}=50mV		C_{tot}			4	pF
Reverse Recovery Time 反向回复时间	IF=IR=10mA, iR=1mA	Trr			8	ns
	I_F=10mA, V_R=6V, i_R=0.1×I_R,R_L=100				4	ns
Junction tambient 热阻 on PC board 50mmx50mmx1.6mm		R_{thJA}			500	K/W
Rectification Efficiency 整流功率 at f=100MHZ, V_{HF}=2V,		ηr	0.45			

Notes: (1)Valid provided that electrodes are kept at ambient temperature.

Dimensions 封装外形尺寸

Dimensions in mm